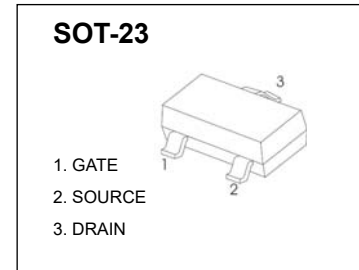


SOT-23 Plastic-Encapsulate MOSFETS
N-Channel MOSFET

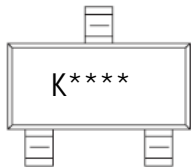
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	240mΩ@10V	2A
	270mΩ@6V	
	280mΩ@4.5V	


FEATURE

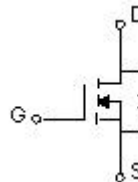
- TrenchFET Power MOSFET
- Low $R_{DS(ON)}$
- Surface Mount Package

APPLICATION

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

MARKING


K = Device Code
* = Date Code*

Equivalent Circuit

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}^*	8	A
Maximum Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}C$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}C$

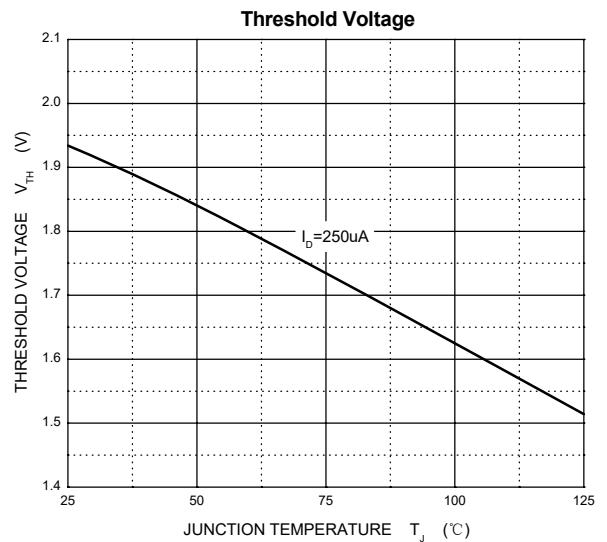
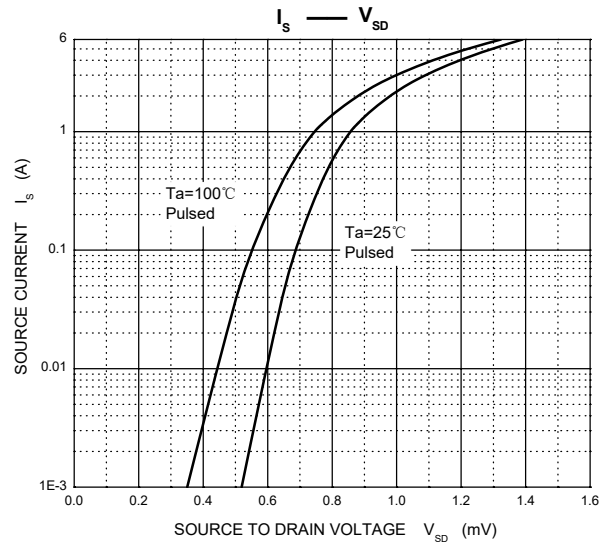
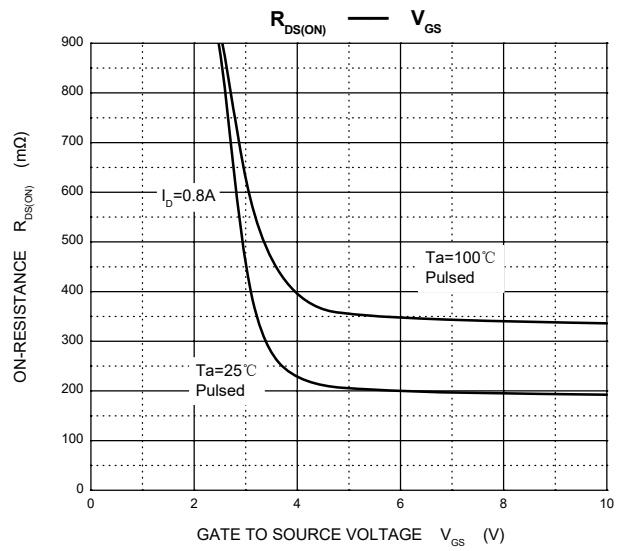
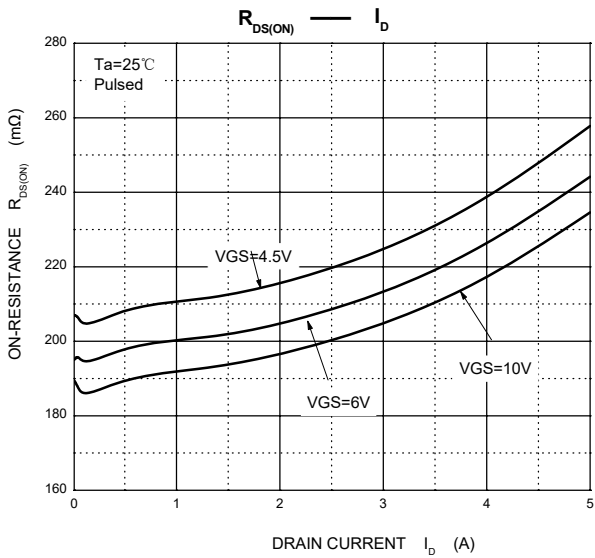
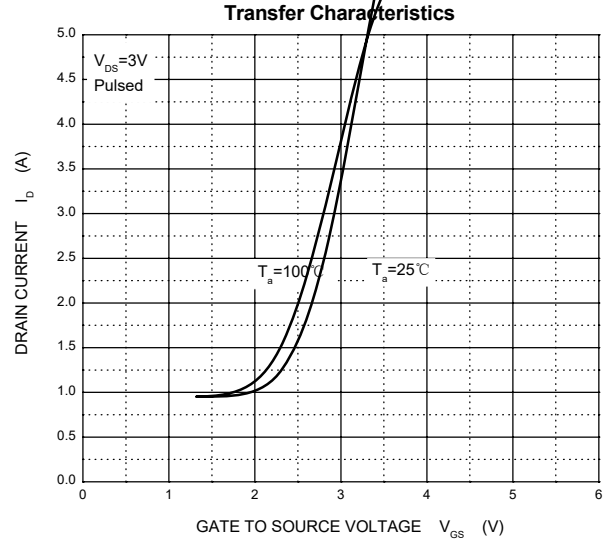
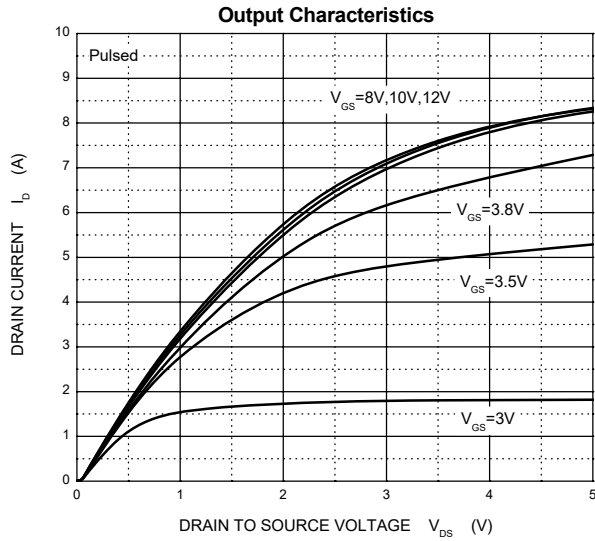
*Repetitive rating: Pulse width limited by junction temperature.

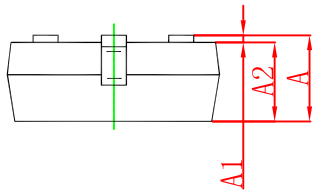
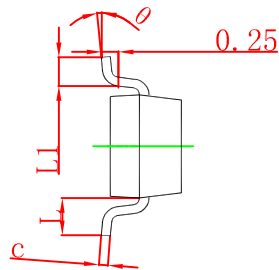
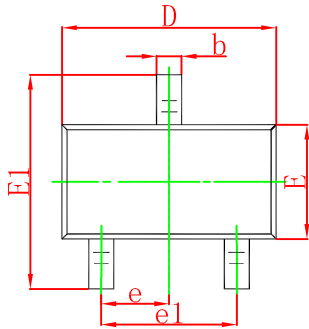
MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

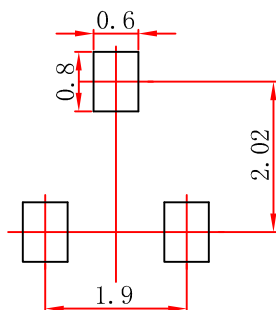
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage(note 1)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0		2.8	V
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.5A$		195	240	m Ω
		$V_{GS} = 6V, I_D = 1A$		200	270	m Ω
		$V_{GS} = 4.5V, I_D = 0.5A$		208	280	m Ω
Forward tranconductance (note 1)	g_{FS}	$V_{DS} = 20V, I_D = 1.5A$		2		S
Diode forward voltage (note 1)	V_{SD}	$I_S = 1.3A, V_{GS} = 0V$			1.2	V
DYNAMIC PARAMETERS (note2)						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		190		pF
Output Capacitance	C_{oss}			22		pF
Reverse Transfer Capacitance	C_{rss}			13		pF
Gate Resistance	R_g	$F = 1MHz$	0.3		2.8	Ω
SWITCHING PARAMETERS (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, V_{GEN} = 4.5V$ $R_L = 39\Omega, R_G = 1\Omega, I_D = 1.3A$			45	ns
Turn-on rise time	t_r				39	ns
Turn-off delay time	$t_{d(off)}$				26	ns
Turn-off fall time	t_f				20	ns
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 4.5V, I_D = 1.6A$			5.8	nC
Gate-Source Charge	Q_{gs}			0.75		nC
Gate-Drain Charge	Q_{gd}			1.4		nC

- Notes :**
1. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.
 2. Guaranteed by design, not subject to production testing.

Typical Characteristics




Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout


- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.